



SESD9DXXC

Transient Voltage Suppressors for ESD Protection

Revision:A

General Description

The SESD9DXXC is designed to protect voltage sensitive components from ESD and transient voltage events. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

Applications

- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Features

- Small Body Outline Dimensions
- Low Body Height
- Peak Power up to 150 Watts @ 8 x 20 µs Pulse
- Low Leakage current
- Response Time is Typically < 1 ns

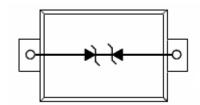
Complies with the following standards IEC61000-4-2

Level 4 15 kV (air discharge) 8 kV(contact discharge)

MIL STD 883E - Method 3015-7 Class 3 25 kV HBM (Human Body Model)

Functional diagram



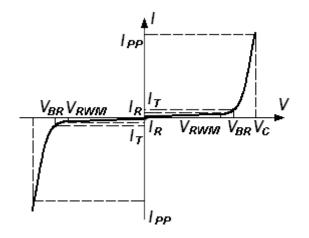


SOD-923

Symbol	Parame	Value	Units	
P _{PP}	Peak Pulse Power (tp = 8/20µs)	150	W	
TL	Maximum lead temperature for solderi	260	°C	
T _{stg}	Storage Temperature Range	-55 to +155	°C	
T _{op}	Operating Temperature Range		-40 to +125	°C
Tj	Maximum junction temperature	150	°C	
	IEC61000-4-2 (ESD)	air discharge contact discharge	±15 ±8	kV
	IEC61000-4-4 (EFT)		40	Α
	ESD Voltage	Per Human Body Model	25	kV
		Per Machine Model	400	V

Electrical Parameter

Symbol	Parameter							
I _{PP}	Maximum Reverse Peak Pulse Current							
V _C	Clamping Voltage @ I _{PP}							
V_{RWM}	Working Peak Reverse Voltage							
I _R	Maximum Reverse Leakage Current @ V _{RWM}							
I _T	Test Current							
V_{BR}	Breakdown Voltage @ I _T							



Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.VF = 0.9V at IF = 10mA

Part Numbers	V _{BR}		la.	V_RWM	L	С	
	Min.	Min. Typ. Ma	Max.	- I _{BR}	RVVM	I _R	Typ. 0v bias
	V	V	V	mA	V	μΑ	pF
SESD9D3V3C	5.1	6.0	6.8	1	3.3	1	20
SESD9D5C	5.6	6.7	7.8	1	5.0	1	11
SESD9D12C	13.3	14.5	15.7	1	12	1	9

^{*}Surge current waveform per Figure 1.

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25 $^{\circ}$ C.

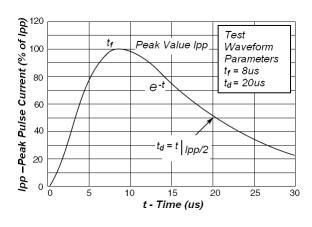


Fig1. Pulse Waveform

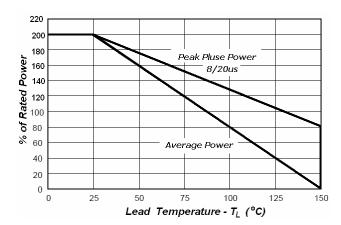


Fig2. Power Derating Curve

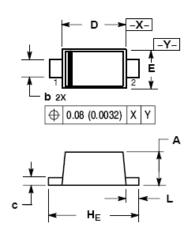
Application Note

Electrostatic discharge (ESD) is a major cause of failure in electronic systems. Transient Voltage Suppressors (TVS) are an ideal choice for ESD protection. They are capable of clamping the incoming transient to a low enough level such that damage to the protected semiconductor is prevented.

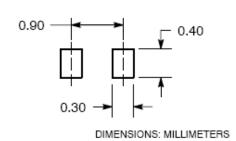
Surface mount TVS offers the best choice for minimal lead inductance. They serve as parallel protection elements, connected between the signal lines to ground. As the transient rises above the operating voltage of the device, the TVS becomes a low impedance path diverting the transient current to ground. The SESD9DXXC is the ideal board evel protection of ESD sensitive semiconductor components.

The tiny SOD-923 package allows design flexibility in the design of high density boards where the space saving is at a premium. This enables to shorten the routing and contributes to hardening against ESD.

SOD-923 Mechanical Data



SOLDERING FOOTPRINT*



SOD-923

Dim	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
А	0.36	0.40	0.43	0.014	0.016	0.017
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
Е	0.55	0.60	0.65	0.022	0.024	0.026
H _E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd. © 2005 SINO-IC – Printed in China – All rights reserved.

SHANGHAI SINO-IC MICROELECTRONICS CO., LTD

Add: Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong,

Shanghai 201203, China

Phone: +86-21-33932402 33932403 33932405 33933508 33933608

Fax: +86-21-33932401

Email: webmaster@sino-ic.com
Website: http://www.sino-ic.com